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AVAILABLE

# MAXIM

## Low-Noise Bias Supply in $\mu$ MAX with Power-OK for GaAsFET PA

MAX881R

### General Description

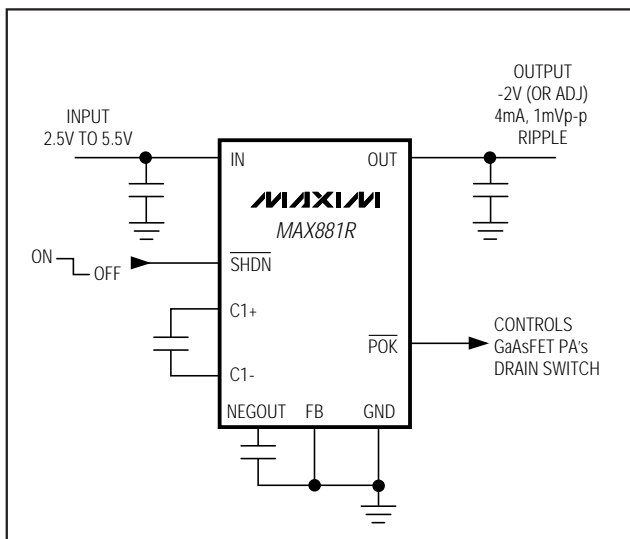
The MAX881R low-noise, inverting power supply is designed for biasing GaAsFET power amplifiers in portable wireless applications. This device is a charge-pump inverter followed by a negative linear regulator. The input voltage range is 2.5V to 5.5V. The output is preset at -2.0V or can be set, using two resistors, to any voltage from -0.5V to  $(-V_{IN} + 0.6V)$ . It can deliver up to 4mA. The internal linear regulator also filters the output to 1mVp-p ripple and noise.

Other features include a power-OK ( $\overline{POK}$ ) output that signals when the negative voltage is within 7.5% of its set point. It protects the GaAsFET by not allowing power to be applied to the GaAsFET's drain until it is properly biased. The signal can be routed either to a microcontroller or directly to a switch at the GaAsFET drain. The MAX881R is available in a space-saving 10-pin  $\mu$ MAX package.

### Applications

Cell Phones  
PCS Phones  
PHS Phones  
Wireless Handsets  
Wireless Modems  
Two-Way Pagers  
Mobile Radios  
Wireless Computers

### Typical Operating Circuit



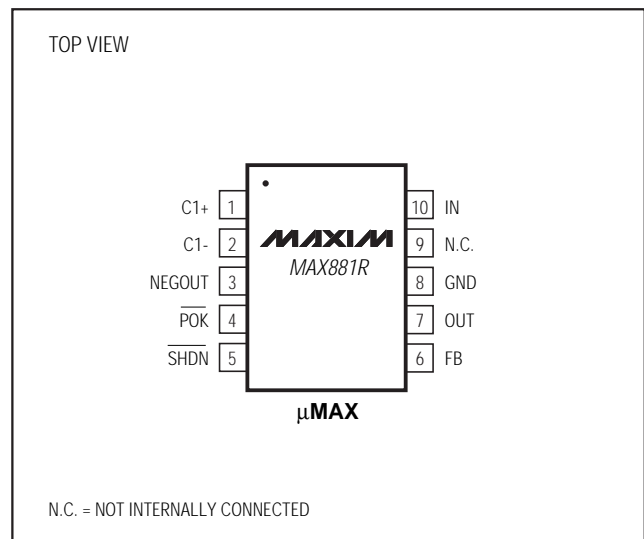
### Features

- ◆ Small  $\mu$ MAX Package
- ◆ 1mVp-p Output Voltage Ripple and Noise
- ◆ Power-OK Signal to Control GaAsFET Drain Switch
- ◆ 0.05 $\mu$ A Logic-Controlled Shutdown
- ◆ 1ms Guaranteed Start-Up
- ◆ 2.5V to 5.5V Input
- ◆ -0.5V to  $(-V_{IN} + 0.6V)$  Output at up to 4mA
- ◆ Operates with One 4.7 $\mu$ F and Three 0.22 $\mu$ F Capacitors (no inductors needed)

### Ordering Information

PART	TEMP. RANGE	PIN-PACKAGE
MAX881REUB	-40°C to +85°C	10 $\mu$ MAX

### Pin Configuration



MAXIM

Maxim Integrated Products 1

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For small orders, phone 408-737-7600 ext. 3468.

# Low-Noise Bias Supply in $\mu$ MAX with Power-OK for GaAsFET PA

## ABSOLUTE MAXIMUM RATINGS

IN to GND .....	-0.3V to +6V	Operating Temperature Range .....	-40°C to +85°C
$\overline{\text{SHDN}}$ to GND.....	-0.3V to +6V	Junction Temperature .....	+150°C
$\overline{\text{POK}}$ to GND .....	-0.3V to +12V	Storage Temperature Range .....	-65°C to +165°C
C1+ to GND .....	-0.3V to ( $V_{\text{IN}} + 0.3\text{V}$ )	Lead Temperature (soldering, 10sec) .....	+300°C
C1-, NEGOUT, OUT, FB to GND .....	-6V to ( $V_{\text{IN}} + 0.3\text{V}$ )		
Continuous Power Dissipation ( $T_{\text{A}} = +70^{\circ}\text{C}$ )			
10-Pin $\mu$ MAX (derate 5.6mW/ $^{\circ}\text{C}$ above +70°C) .....	444mW		

**Note 1:** The output may be shorted to NEGOUT or GND if the package power dissipation is not exceeded. Typical short-circuit current is 35mA.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

## ELECTRICAL CHARACTERISTICS

(Circuit of Figure 3,  $V_{\text{IN}} = +3.6\text{V}$ , FB = GND,  $R_{\text{L}} = \infty$ ,  $\overline{\text{SHDN}} = \text{IN}$ ,  $T_{\text{A}} = -40^{\circ}\text{C}$  to  $+85^{\circ}\text{C}$ , unless otherwise noted. Typical values are at  $T_{\text{A}} = +25^{\circ}\text{C}$ .) (Note 2)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS	
Supply Voltage Range	$V_{\text{IN}}$		2.5		5.5	V	
Preset Output Voltage	$V_{\text{OUT}}$	$V_{\text{IN}} \geq 2.7\text{V}$ , $I_{\text{OUT}} = 0$ to 4mA	-2.1	-2.0	-1.9	V	
Adjustable Output Voltage Range	$V_{\text{OUT}}$	$V_{\text{IN}} \geq 2.5\text{V}$ , $I_{\text{OUT}} = 0$ to 4mA	$-(V_{\text{IN}} - 0.6)$		-0.5	V	
FB Voltage	$V_{\text{FB}}$	$V_{\text{IN}} \geq 2.5\text{V}$ , $I_{\text{OUT}} = 0$ to 4mA	$T_{\text{A}} = +25^{\circ}\text{C}$	-0.515	-0.5	-0.485	V
			$T_{\text{A}} = 0^{\circ}\text{C}$ to $+85^{\circ}\text{C}$	-0.525		-0.475	
			$T_{\text{A}} = -40^{\circ}\text{C}$ to $+85^{\circ}\text{C}$	-0.535		-0.465	
FB Input Current		$V_{\text{FB}} = -0.5\text{V}$		-10	-100	nA	
Supply Current	$I_{\text{Q}}$			500	950	$\mu\text{A}$	
Shutdown Supply Current	$I_{\text{SHUT}}$	$\overline{\text{SHDN}} = \text{GND}$		0.05	1	$\mu\text{A}$	
Output Load Regulation		$V_{\text{IN}} \geq 2.7\text{V}$ , $I_{\text{OUT}} = 0$ to 4mA		2	6	mV/mA	
Output Ripple		$I_{\text{OUT}} = 4\text{mA}$ , circuit of Figure 3b		1		mVp-p	
Oscillator Frequency	$f_{\text{OSC}}$		80	100	120	kHz	
$\overline{\text{POK}}$ Threshold		FB = OUT	90	92.5	95	% of $V_{\text{OUT}}$	
$\overline{\text{POK}}$ Output Level		$V_{\text{IN}} \geq 2.5\text{V}$ , sinking 1mA			100	mV	
$\overline{\text{POK}}$ Off Leakage Current		$V_{\overline{\text{POK}}} = 11\text{V}$			1	$\mu\text{A}$	
$\overline{\text{SHDN}}$ Input High Voltage	$V_{\text{IH}}$	$V_{\text{IN}} = 5.5\text{V}$	2.2			V	
$\overline{\text{SHDN}}$ Input Low Voltage	$V_{\text{IL}}$	$V_{\text{IN}} = 2.5\text{V}$			0.35	V	
$\overline{\text{SHDN}}$ Input Current	$I_{\overline{\text{SHDN}}}$	Connected to IN or GND			$\pm 1$	$\mu\text{A}$	
$\overline{\text{SHDN}}$ Input Capacitance	$C_{\text{IN}}$			10		pF	
Start-Up Time	$t_{\text{START}}$	$V_{\text{IN}} = 3\text{V}$ , $R_{\text{L}} = 500\Omega$ , $V_{\overline{\text{SHDN}}} = 0$ to $V_{\text{IN}}$ , $\overline{\text{POK}}$ goes low			1	ms	

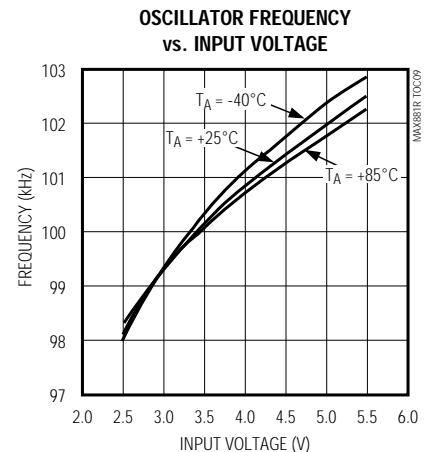
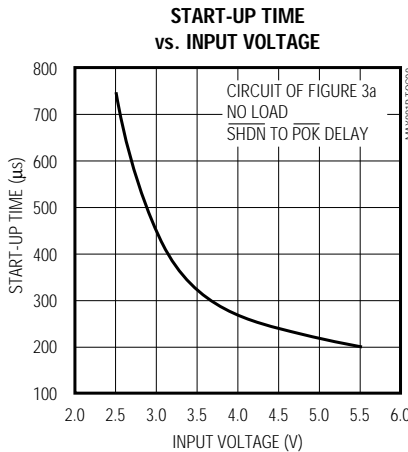
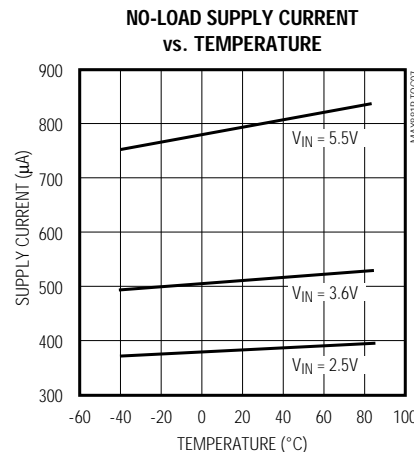
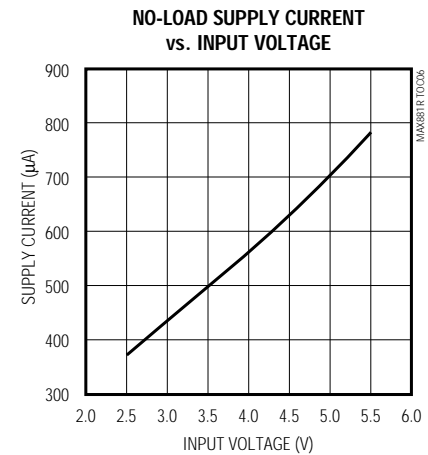
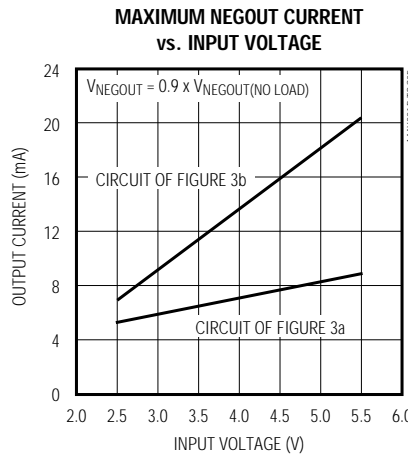
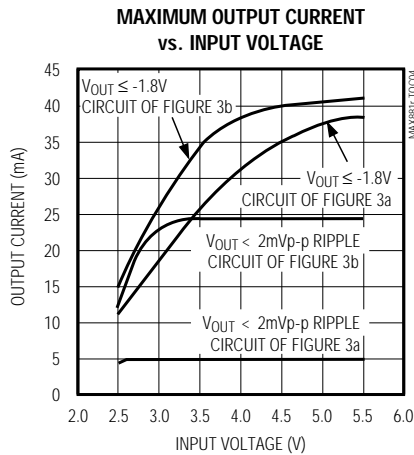
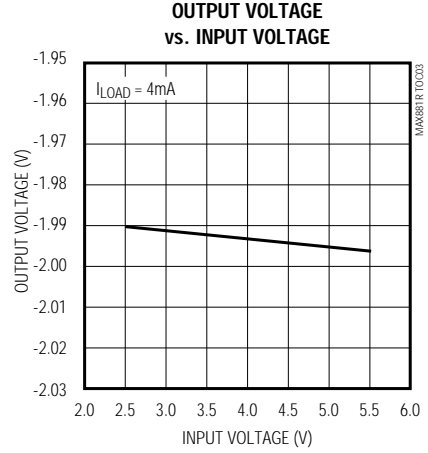
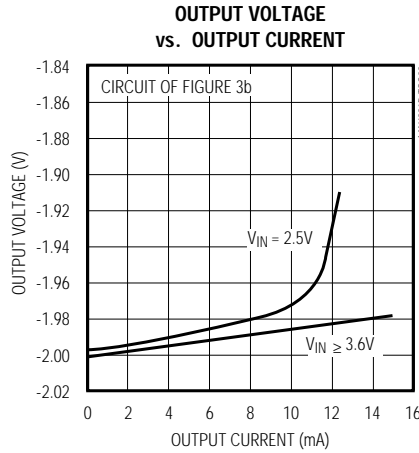
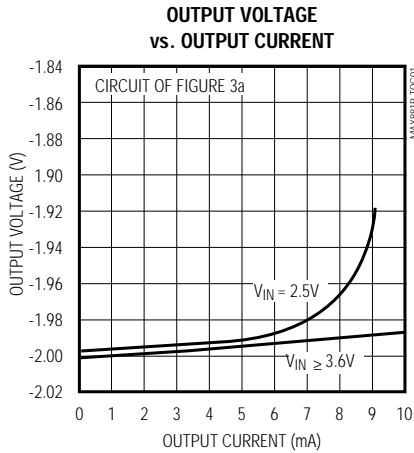
**Note 2:** Specifications to  $-40^{\circ}\text{C}$  are guaranteed by design, not production tested.

# Low-Noise Bias Supply in $\mu$ MAX with Power-OK for GaAsFET PA

## Typical Operating Characteristics

(Circuit of Figure 3,  $V_{IN} = 3.6V$ ,  $T_A = +25^\circ C$ , unless otherwise noted.)

MAX881R

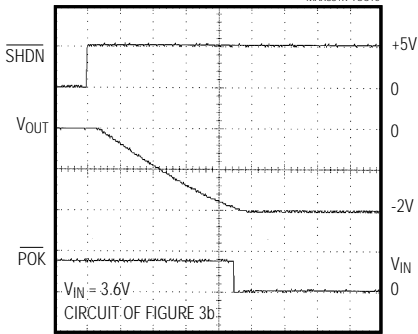


# Low-Noise Bias Supply in $\mu$ MAX with Power-OK for GaAsFET PA

## Typical Operating Characteristics (continued)

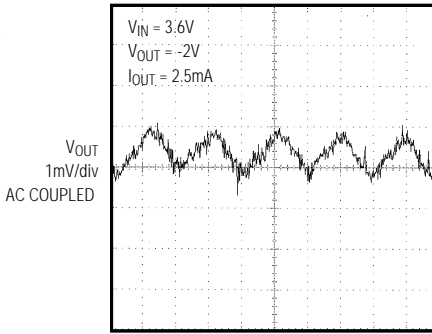
(Circuit of Figure 3,  $V_{IN} = 3.6V$ ,  $T_A = +25^\circ C$ , unless otherwise noted.)

**START-UP FROM SHUTDOWN (NO LOAD)**  
MAX881R-TOC10



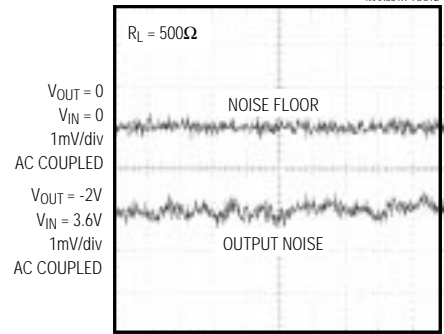
100µs/div

**OUTPUT NOISE AND RIPPLE (CIRCUIT OF FIGURE 3a)**  
MAX881R-TOC11



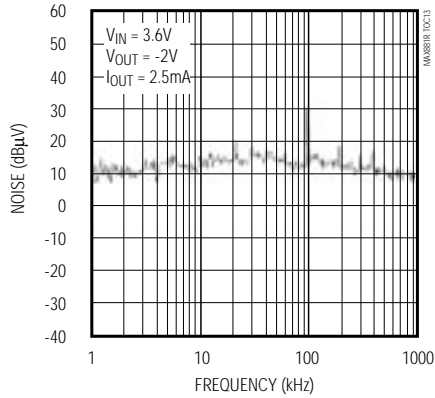
5µs/div

**OUTPUT NOISE AND RIPPLE (CIRCUIT OF FIGURE 3b)**  
MAX881R-TOC12

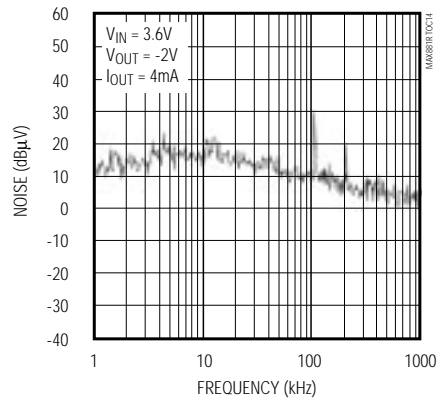


10µs/div

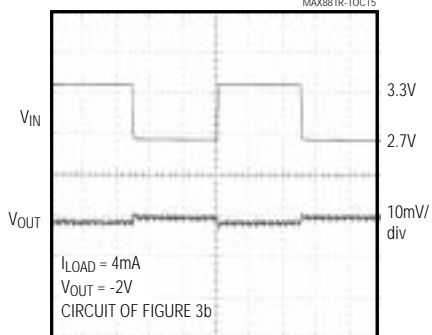
**OUTPUT NOISE SPECTRUM (CIRCUIT OF FIGURE 3a)**  
MAX881R-TOC13



**OUTPUT NOISE SPECTRUM (CIRCUIT OF FIGURE 3b)**  
MAX881R-TOC14

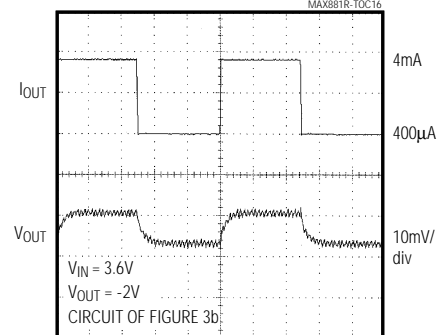


**LINE-TRANSIENT RESPONSE**  
MAX881R-TOC15



2ms/div

**LOAD-TRANSIENT RESPONSE**  
MAX881R-TOC16



100µs/div

# Low-Noise Bias Supply in $\mu$ MAX with Power-OK for GaAsFET PA

MAX881R

## Pin Description

PIN	NAME	FUNCTION
1	C1+	Positive Terminal for C1
2	C1-	Negative Terminal for C1
3	NEGOUT	Negative Output Voltage (unregulated)
4	$\overline{\text{POK}}$	Active-Low, Open-Drain Power-OK Output. Goes low when OUT reaches 92.5% of its set value.
5	$\overline{\text{SHDN}}$	Active-Low, Logic-Level Shutdown Input. Connect to IN for normal operation. Do not leave this pin unconnected.
6	FB	Dual-Mode™ Feedback Input. When FB is connected to GND, the output is preset to -2V. To select other voltages, connect FB to an external resistor-divider (Figure 4). Do not leave this pin unconnected.
7	OUT	Regulated Negative Output Voltage
8	GND	Ground
9	N.C.	No Connection. Not internally connected.
10	IN	Positive Power-Supply Input

Dual-Mode is a trademark of Maxim Integrated Products.

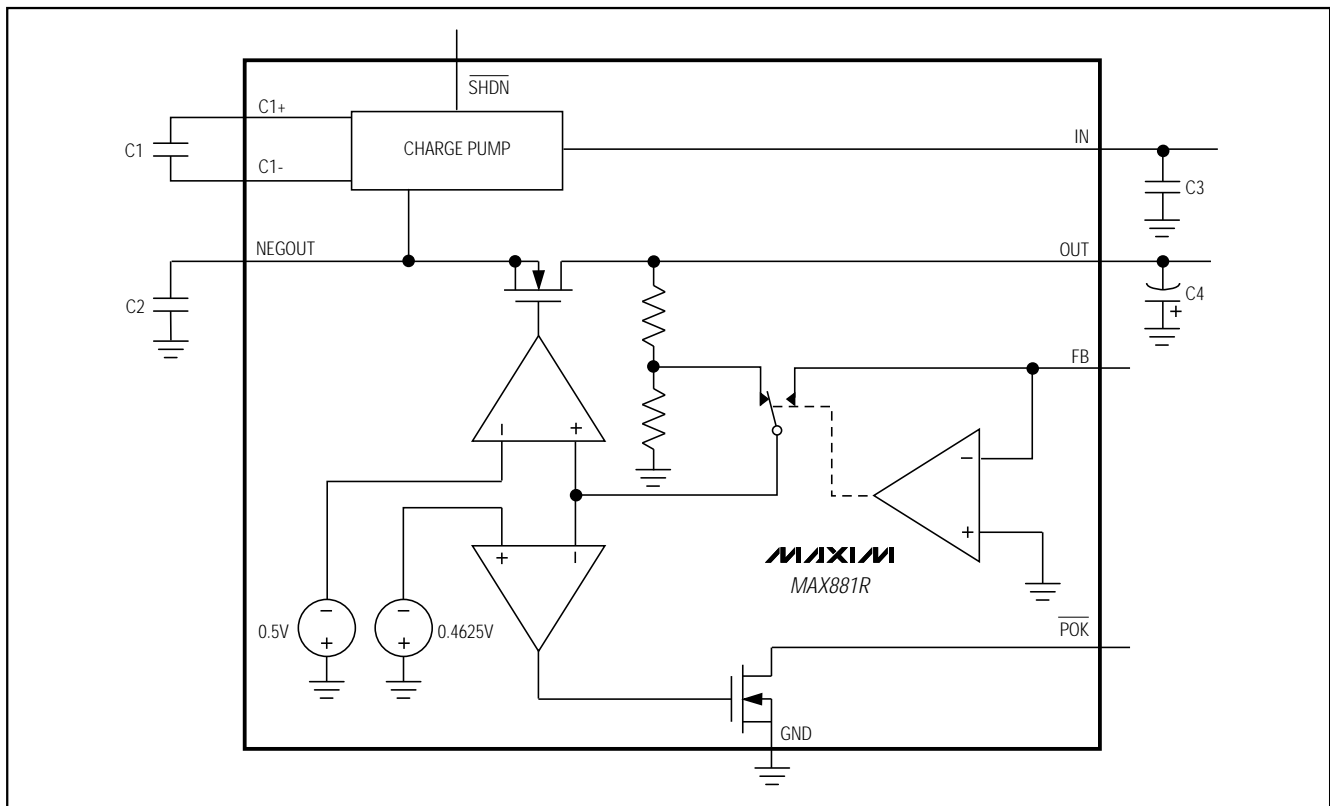


Figure 1. Functional Diagram

# Low-Noise Bias Supply in $\mu$ MAX with Power-OK for GaAsFET PA

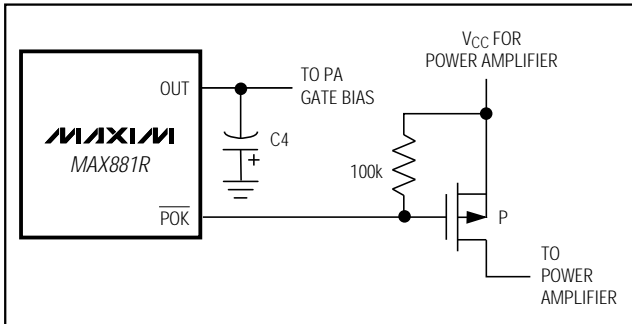


Figure 2. Using the  $\overline{\text{POK}}$  Function

## Detailed Description

The MAX881R, a low-noise, inverting, regulated charge-pump power supply, is designed for biasing GaAsFET devices such as power-amplifier modules in cellular handsets.

The applied input voltage ( $V_{\text{IN}}$ ) is inverted to a negative voltage at NEGOUT by a capacitive charge pump. This voltage is regulated by an internal linear regulator at OUT (Figure 1). With FB connected to GND,  $V_{\text{OUT}}$  is regulated at -2V. Alternatively, use a voltage-divider at FB to adjust the output voltage between -0.5V and  $-(V_{\text{IN}} - 0.6\text{V})$  (see the section *Setting the Output Voltage*). The internal linear regulator reduces the ripple noise induced by the charge-pump inverter to 1mVp-p at OUT (circuit of Figure 3b). In addition, the excellent AC rejection of the linear regulator attenuates noise from the incoming supply.

### Power-OK Signal

The MAX881R has an active-low, open-drain, power-OK ( $\overline{\text{POK}}$ ) output. This output goes low when OUT reaches 92.5% of the regulated output voltage.  $\overline{\text{POK}}$  can be used to drive the gate of a P-MOSFET that switches power to the GaAsFET power amplifier (Figure 2), thereby ensuring that the power amplifier is not powered before the required negative bias voltage is present.

Use a 50k $\Omega$  or larger pull-up resistor to signal a logic high when  $\overline{\text{POK}}$  goes high impedance.

### Shutdown Mode

The MAX881R features a shutdown mode that reduces supply current to less than 1 $\mu$ A over temperature. SHDN is an active-low, logic-level input. Start-up time coming out of shutdown mode is typically 0.5ms. OUT and NEGOUT are switched to GND in shutdown mode.

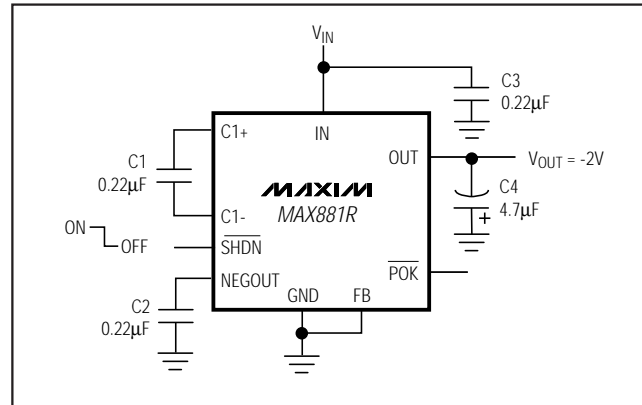


Figure 3a. Standard Application Circuit for Minimum Capacitor Values

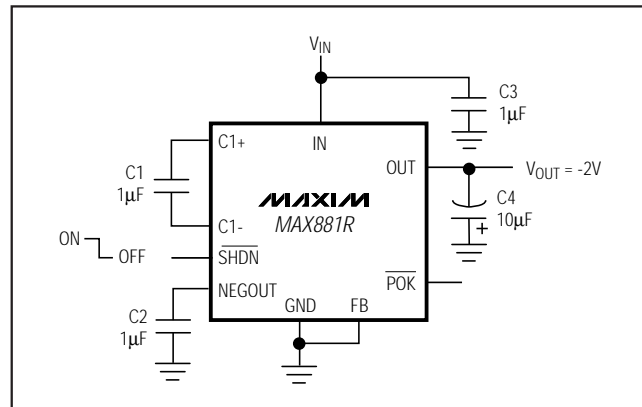


Figure 3b. Standard Application Circuit for Minimum Output Noise

## Applications Information

### Setting the Output Voltage

Select either a fixed or adjustable output for the MAX881R. Connect FB to GND for a fixed -2V output (Figure 3). Select an alternative output voltage by connecting FB to the midpoint of a resistor-divider from OUT to GND (Figure 4). When operating under full load (4mA), the voltage at IN should be at least 0.6V higher than the absolute voltage required at OUT. Note that the minimum input voltage required for operation is 2.5V, regardless of the desired output voltage. Choose R1 to be between 100k $\Omega$  and 400k $\Omega$  and calculate R2. For greater accuracy, use resistors with 1% or better tolerance.

$$R2 = R1 (2 \times |V_{\text{OUT}}| - 1)$$

# Low-Noise Bias Supply in $\mu$ MAX with Power-OK for GaAsFET PA

MAX881R

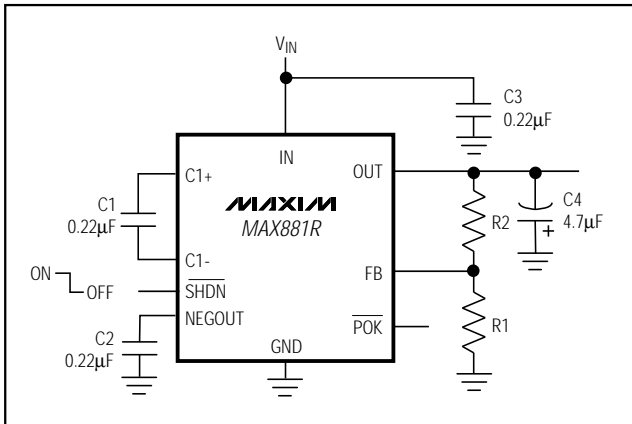


Figure 4. Adjustable Output Configuration

## Capacitors

Use capacitors with a low effective series resistance (ESR) to maintain a low dropout voltage ( $V_{IN} - |V_{OUT}|$ ). The overall dropout voltage is a function of the output resistance of the charge pump and the voltage drop across the linear regulator (N-channel pass transistor). At the 100kHz charge-pump switching frequency, output resistance is a function of the value of C1 and the ESR of C1 and C2. Therefore, increasing C1 and minimizing the ESR of the charge-pump capacitors minimizes dropout voltage.

The output resistance of the entire circuit (in dropout) is approximately:

$$R_{OUT} = R_O + 4 \times ESR_{C1} + ESR_{C2} + 1 / (f_s \times C1) + R(\text{linear regulator})$$

Where  $R(\text{linear regulator})$  (the output impedance of the linear regulator) is approximately  $2\Omega$  and  $R_O$  (the resis-

tance of the internal switches) is typically  $10\Omega$ . When regulating, the output resistance of the circuit is simply the linear-regulator load regulation ( $2\text{mV/mA}$ ).

C1, C2, and C3 should be  $0.22\mu\text{F}$  capacitors with less than  $0.4\Omega$  ESR. C4 should be a  $4.7\mu\text{F}$  capacitor with less than  $0.1\Omega$  ESR. Larger capacitor values can be used ( $C1 = C2 = C3 = 1\mu\text{F}$ ,  $C4 = 10\mu\text{F}$ ) to reduce output noise and ripple ( $1\text{mVp-p}$ ), at the expense of cost and board space. All capacitors should be either ceramic or surface-mount chip tantalum (Figures 3a and 3b).

## Layout and Grounding

Good layout is important for good noise performance. To optimize the layout:

- 1) Mount all components as close together as possible.
- 2) Keep traces short to minimize parasitic inductance and capacitance, especially connections to FB.
- 3) Use a ground plane.

## Noise and Ripple Measurement

Accurately measuring the output noise and ripple is a challenge. Slight momentary differences in ground potential between the circuit and the oscilloscope (which result from the charge pump's switching action) cause ground currents in the probes' wires, inducing sharp voltage spikes. For best results, measure directly across the output capacitor (C4). Do not use the ground lead of the probe; instead, remove the probe's tip cover and touch the ground ring on the probe directly to C4's ground terminal. This direct connection gives the most accurate noise and ripple measurement.

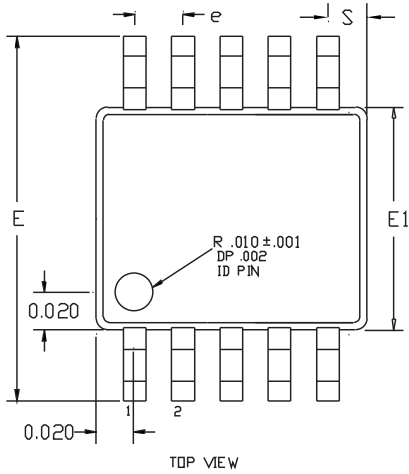
## Chip Information

TRANSISTOR COUNT: 413

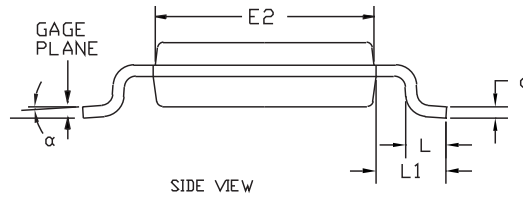
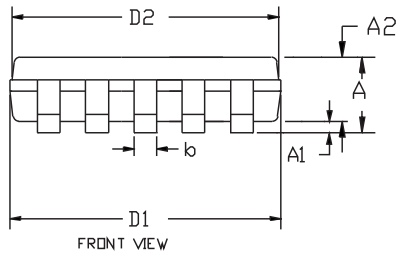
# Low-Noise Bias Supply in $\mu$ MAX with Power-OK for GaAsFET PA

## Package Information

10LUMAX8E/PS



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.037	0.043	0.939	1.092
A1	0.002	0.006	0.051	0.152
A2	0.030	0.038	0.762	0.965
D1	0.112	0.124	2.845	3.150
D2	0.110	0.122	2.794	3.099
E1	0.112	0.124	2.845	3.150
E2	0.110	0.122	2.794	3.099
E	0.185	0.201	4.699	5.105
L	0.0155	0.0275	0.394	0.699
L1	0.037 REF		0.940 REF	
b	0.007	0.0106	0.177	0.270
e	0.0197 BSC		.500 BSC	
c	0.0035	0.0078	0.090	0.200
S	0.0196 REF		.498 REF	
$\alpha$	0°	6°	0°	6°



- NOTES:
1. D&E DO NOT INCLUDE MOLD FLASH.
  2. MOLD FLASH OR PROTRUSIONS NOT TO EXCEED .15mm(.006").
  3. CONTROLLING DIMENSION: INCHES

**MAXIM**  
 PROPRIETARY INFORMATION  
 TITLE:  
 PACKAGE OUTLINE, 10L MICRO MAX  
 APPROVAL: \_\_\_\_\_ DOCUMENT CONTROL NO. 21-0061 REV B 1/1